Schottky Barrier Diode

Features

1. High reliability
2. Low reverse current and low forward voltage

Applications

Low current rectification and high speed switching

Construction

Silicon epitaxial planar

Absolute Maximum Ratings

T_j=25℃

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage		1N60	V_{RRM}	40	V
		1N60P	V_{RRM}	45	V
Peak forward surge current	t_p≦1 s	1N60	I_{FSM}	150	mA
		1N60P	I_{FSM}	500	mA
Forward continuous current	T_a=25℃	1N60	I_F	30	mA
		1N60P	I_F	50	mA
Storage temperature range			T_{stg}	-65~+125	℃

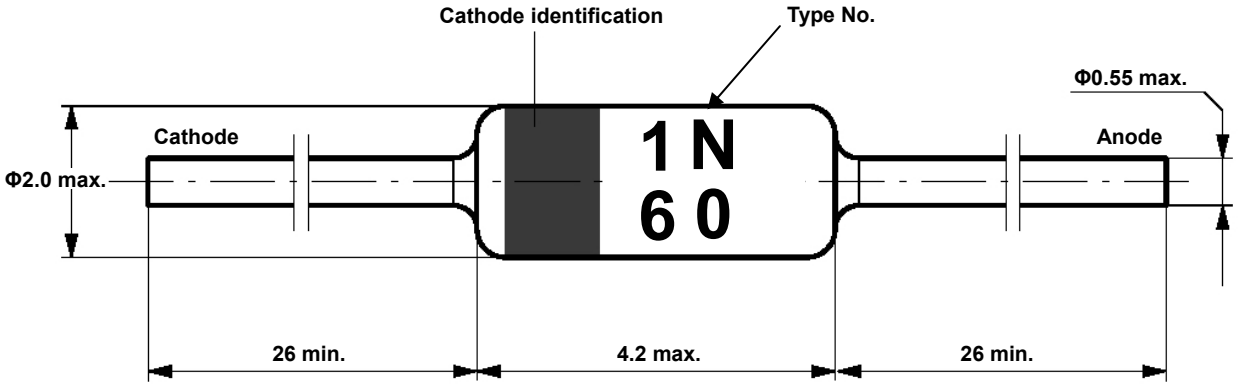
Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

Electrical Characteristics

T_j=25℃

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=1mA	1N60	V_F		0.32	0.5	V
		1N60P	V_F		0.24	0.5	V
	I_F=30mA	1N60	V_F		0.65	1.0	V
	I_F=200mA	1N60P	V_F		0.65	1.0	V
Reverse current	V_R=15V	1N60	I_R		0.1	0.5	μA
		1N60P	I_R		0.5	1.0	μA
Junction capacitance	V_R=1V, f=1MHz	1N60	C_J		2.0		pF
	V_R=10V, f=1MHz	1N60P	C_J		6.0		pF
Reverse recovery time	I_F=I_R=1mA I_{rr}=1mA R_C=100Ω		t_{rr}			1.0	ns

Dimensions in mm



Standard Glass Case
JEDEC DO-35

Marking